



ACE3401A

P-Channel Enhancement Mode Field Effect Transistor

Description

The ACE3401A uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications. Standard product ACE3401A is Pb-free (meets ROHS & Sony 259 specifications).

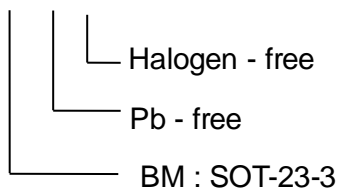
Features

- $V_{DS} (V) = -30V$
- $I_D = -4.0 A (V_{GS} = -10V)$
- $R_{DS(ON)} < 50m\Omega (V_{GS} = -10V)$
- $R_{DS(ON)} < 65m\Omega (V_{GS} = -4.5V)$
- $R_{DS(ON)} < 120m\Omega (V_{GS} = -2.5V)$

Absolute Maximum Ratings ($T_A=25^\circ C$, unless otherwise noted)

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current ^{NOTEA}	I_D	$T_A=25^\circ C$	-4.0
		$T_A=70^\circ C$	-3.5
Pulsed Drain Current ^{NOTEB}	I_{DM}	-25	A
Power Dissipation ^{NOTEA}	P_D	$T_A=25^\circ C$	1.4
		$T_A=70^\circ C$	1
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

ACE3401A XX + H





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Notes

1. All dimensions are in millimeters.
 2. Tolerance $\pm 0.10\text{mm}$ (4 mil) unless otherwise specified
 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
 4. Dimension L is measured in gauge plane.
 5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.
- ACE Technology Co., LTD. <http://www.ace-ele.com/>